

GOFORD MOSFET-GT025N06D5 by SGT Technology

GOFORD GT025N06D5 N-MOS 60V DFN8L-5*6

Datasheet link: <http://www.gofordsemi.com/products-detail.php?ProId=549>

Cross reference to: DIODES DMNH6009SPS ; Alpha&Omega AONS62614;

ONSEMI FDMS86520; ONSEMI FDMS030N06B



GT025N06D5 is produced by advanced SGT (Shield Gate Trench MOSFET) technology with extremely low R_{sp} . It especially lowers the miller capacitor and greatly reduces switching loss. It improves the avalanche while optimizes R_{dson} and Q_g .

GT025N06D5's Advantages:

1. Advanced SGT technology; extremely low R_{dson} ; excellent switching characteristics; Better FOM; Better power dissipation; Less conduction loss;

2. Comparing with the normal trench technology, the SGT technology optimizes the parameters of C_{iss}/Q_g and leaves more space for MOSFET driver designing and fabricating.

3. Better reliability by optimizing the EAS characteristics to deal with the exceptional working states in the application.

GT025N06D5's APPLICATION :

- ✓ Motor Control(Drone, Power Tools, Cooling Fan and so on);
- ✓ LED DRIVER;
- ✓ BMS;
- ✓ Synchronous Rectifier circuit;
- ✓ High-Power Supply for telecom Station & Server.

